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Bong-Cheol Kim

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U.S. PATENT DOCUMENTS

*Exam. Init.	Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate

FOREIGN PATENT DOCUMENT

	Document No.	Date	Country	Class	SubClass	Translator Yes No
DL	9 1 1 6 6 3 8	4/28/02	✓ Japan (w/abstract)			
DL	0 3 0 2 2 4 1 0	1/30/91	✓ Japan (w/abstract)			
DL	6 1 1 7 9 5 2 3	12/8/86	✓ Japan (w/abstract)			

OTHER DOCUMENTS (including Author, Title Date, Pertinent Pages, Etc.)

DL	✓	"Optical Process for Liff-off of Group III-Nitride Films", by Kelly et al., phys. stat. sol. (a) 159, R3 (1997)
DL	✓	"Damage-free Separation of GaN Thin Films From Sapphire Substrates", by Wong et al., <u>Applied Physics Letters</u> , Vol. 72, No. 5, February 2, 1998, pages 599-601
DL	✓	"Fabrication of Thin-Film InGaN Light-emitting Diode Membranes by Laser Lift-off", by Wong et al., <u>Applied Physics Letters</u> , Vol. 75, No. 10, September 6, 1999, pages 1360-1362
DL	✓	"Large Free-Standing GaN Substrates by Hydride Vapor Phase Epitaxy and Laser-Induced Liff-off", by Kelly et al., <u>Jpn. J. Appl. Phys.</u> , Vol. 38 (1999) pages L217-L219

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Examiner

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3/30/03

* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.